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Pa Form PTO-1449 U.S. Department of Commerce (Rev. 8-83)Patern and Tredemark Office Attorney Docket No. 0756-1653 Serial No. 08/818,884 INFORMATION DISCLOSURE STATEMENT Applicant: Shunpei YAMAZAKI, et al. (Use several sheets if necessary) Filing Dam: September 5, 2000 Group: 2871 FOREIGN PATENT DOCUMENTS Document Number Date Country Class Subclass Translation Yes 3 59-072128\* No 04/1984 JР 59-115574+ Full 07/1984 JP 60-245174+ Full 12/1985 JР 60-245173\* Full 12/1985 JР 60-245172\* Abstract 12/1985 JP 61-126595\* Pull 06/1986 JP 61-141174\* Abstract 06/1986 JР 62-126677\* Full 06/1987 JP 62-147759 Abstract 07/01/87 JP 62-160425 Abstract 07/1987 P 63-100777+ Abstract 05/1988 JP 63-219172\* Abstract 09/1988 P 63-237571\* Abstract 10/1988 JP 63-237570+ Abstract 10/1988 ĴΡ 63-29729 Abstract 02/08/88 JP 1-30272\* Abstract 02/1989 JΡ 64-68724\* Abstract 03/1989 JР Abstract 64-68728+ 03/1989 JР **B**~ 1-107237\* Abstract 04/1989 JР Examiner BNYVYEN X Date Considered 18/04 EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Submitted with IDS of October 24, 2000

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Complete If Known 08/818,884 Application Number INFORMATION DISCLOSURE March 17, 1997 Filing Date STATEMENT BY APPLICANT Shunpei YAMAZAKI et al. First Named Inventor (use as many sheets as necessary) 2871 Group Art Unit Examiner Name D. Nguyen Sheet of Attorney Docket Number 0756-1653

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